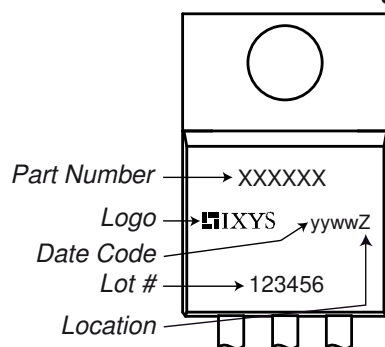


Schottky				Ratings			
Symbol	Definition	Conditions		min.	typ.	max.	Unit
V_{RSM}	max. non-repetitive reverse blocking voltage	$T_{VJ} = 25^{\circ}\text{C}$				200	V
V_{RRM}	max. repetitive reverse blocking voltage	$T_{VJ} = 25^{\circ}\text{C}$				200	V
I_R	reverse current, drain current	$V_R = 200\text{ V}$	$T_{VJ} = 25^{\circ}\text{C}$			250	μA
		$V_R = 200\text{ V}$	$T_{VJ} = 125^{\circ}\text{C}$			2.5	mA
V_F	forward voltage drop	$I_F = 15\text{ A}$	$T_{VJ} = 25^{\circ}\text{C}$			0.94	V
		$I_F = 30\text{ A}$				1.10	V
		$I_F = 15\text{ A}$	$T_{VJ} = 125^{\circ}\text{C}$			0.78	V
		$I_F = 30\text{ A}$				0.95	V
I_{FAV}	average forward current	$T_C = 155^{\circ}\text{C}$ rectangular $d = 0.5$	$T_{VJ} = 175^{\circ}\text{C}$			15	A
V_{F0}	threshold voltage	} for power loss calculation only		$T_{VJ} = 175^{\circ}\text{C}$		0.53	V
r_F	slope resistance					10.8	m Ω
R_{thJC}	thermal resistance junction to case					1.75	K/W
R_{thCH}	thermal resistance case to heatsink				0.50		K/W
P_{tot}	total power dissipation	$T_C = 25^{\circ}\text{C}$				85	W
I_{FSM}	max. forward surge current	$t = 10\text{ ms}; (50\text{ Hz}), \text{ sine}; V_R = 0\text{ V}$	$T_{VJ} = 45^{\circ}\text{C}$			320	A
C_J	junction capacitance	$V_R = 48\text{ V}$ $f = 1\text{ MHz}$	$T_{VJ} = 25^{\circ}\text{C}$		47		pF

Package TO-220			Ratings			
Symbol	Definition	Conditions	min.	typ.	max.	Unit
I_{RMS}	RMS current	per terminal ¹⁾			35	A
T_{VJ}	virtual junction temperature		-55		175	°C
T_{op}	operation temperature		-55		150	°C
T_{stg}	storage temperature		-55		150	°C
Weight				2		g
M_D	mounting torque		0.4		0.6	Nm
F_C	mounting force with clip		20		60	N

Product Marking



Part description

D = Diode
 S = Schottky Diode
 A = low VF
 30 = Current Rating [A]
 C = Common Cathode
 200 = Reverse Voltage [V]
 PB = TO-220AB (3)

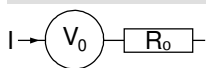
Ordering	Ordering Number	Marking on Product	Delivery Mode	Quantity	Code No.
Standard	DSA30C200PB	DSA30C200PB	Tube	50	507014

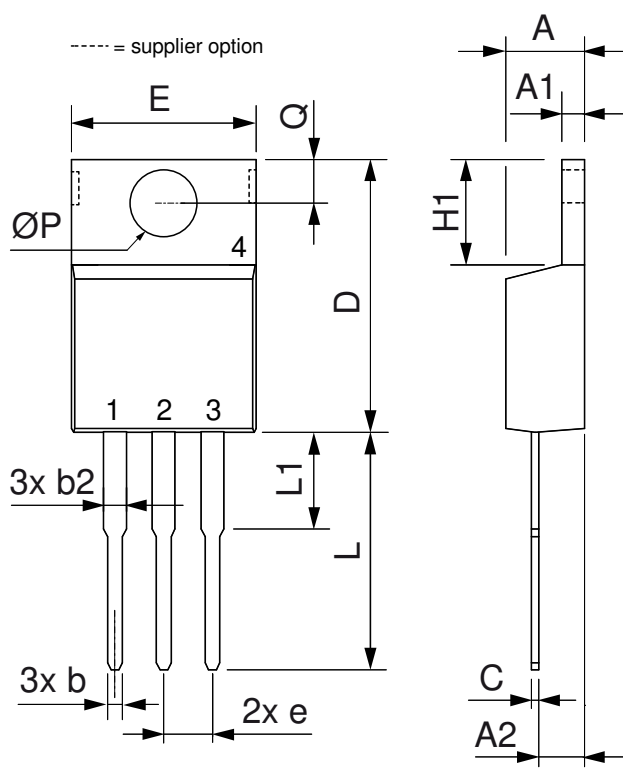
Similar Part	Package	Voltage class
DSA30C200IB	TO-262 (I2Pak) (3)	200
DSA30C200PC	TO-263AB (D2Pak) (2)	200

Equivalent Circuits for Simulation

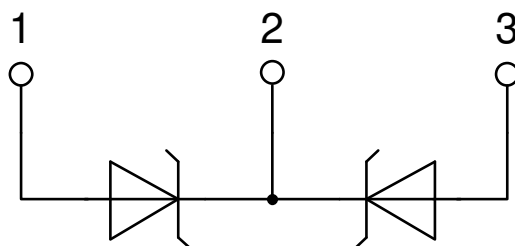
* on die level

$T_{VJ} = 175^{\circ}\text{C}$

		Schottky	
$V_{0\max}$	threshold voltage	0.53	V
$R_{0\max}$	slope resistance *	7.6	mΩ

Outlines TO-220


Dim.	Millimeter		Inches	
	Min.	Max.	Min.	Max.
A	4.32	4.82	0.170	0.190
A1	1.14	1.39	0.045	0.055
A2	2.29	2.79	0.090	0.110
b	0.64	1.01	0.025	0.040
b2	1.15	1.65	0.045	0.065
C	0.35	0.56	0.014	0.022
D	14.73	16.00	0.580	0.630
E	9.91	10.66	0.390	0.420
e	2.54	BSC	0.100	BSC
H1	5.85	6.85	0.230	0.270
L	12.70	13.97	0.500	0.550
L1	2.79	5.84	0.110	0.230
ØP	3.54	4.08	0.139	0.161
Q	2.54	3.18	0.100	0.125



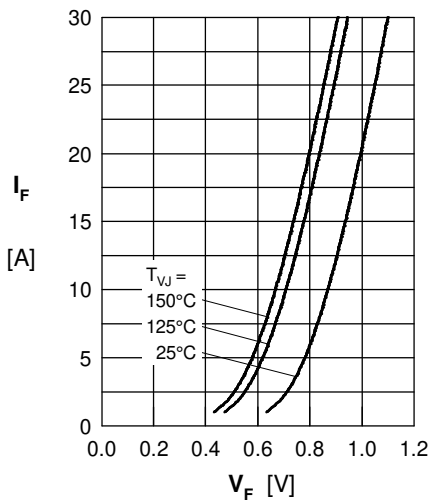
Schottky


Fig. 1 Maximum forward voltage drop characteristics

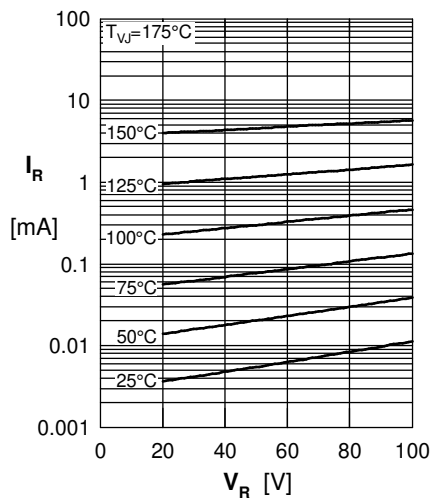
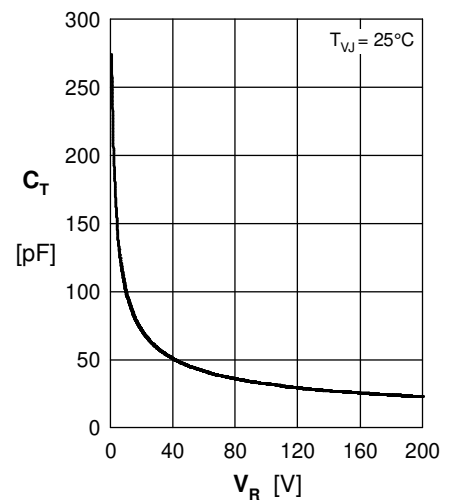
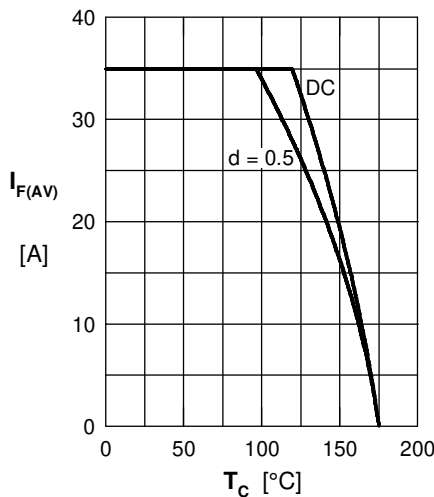
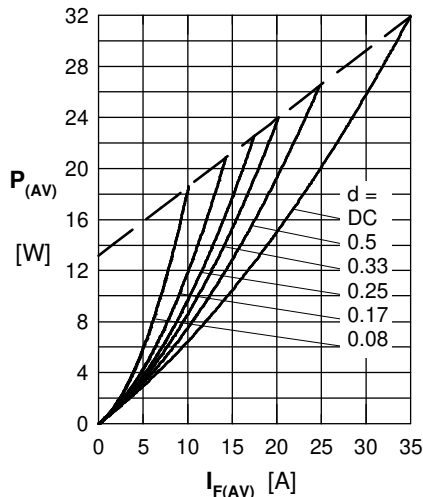

 Fig. 2 Typ. reverse current I_R vs. reverse voltage V_R

 Fig. 3 Typ. junction capacitance C_T vs. reverse voltage V_R

 Fig. 4 Average forward current $I_{F(AV)}$ vs. case temperature T_C


Fig. 5 Forward power loss characteristics

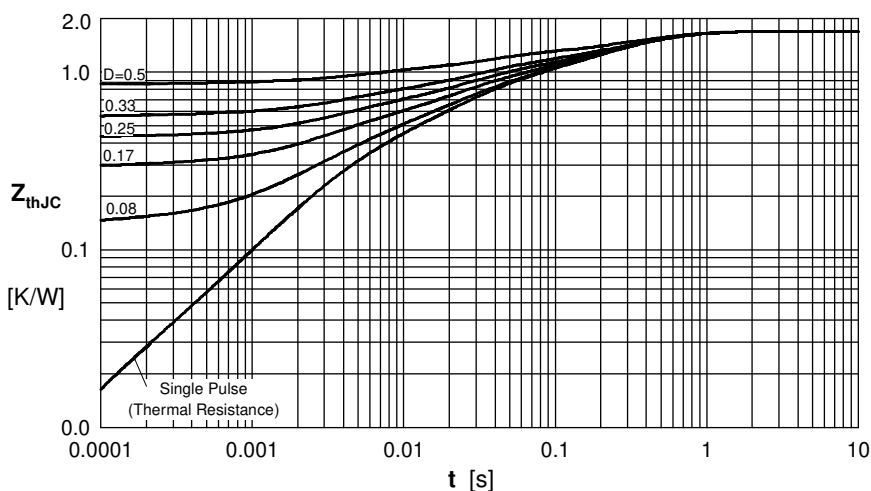


Fig. 6 Transient thermal impedance junction to case

Note: All curves are per diode